

209284US99

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF:

Zhiyi YU, et al.

SERIAL NO:

09/842,734

GAU:

2811

FILED:

April 26, 2001

EXAMINER: HU, S.

. . .

FOR:

STRUCTURE AND METHOD FOR FABRICATING SEMICONDUCTOR STRUCTURES AND DEVICES

USING BINARY METAL OXIDE LAYERS

INFORMATION DISCLOSURE STATEMENT UNDER 37 CFR 1.97

COMMISSIONER FOR PATENTS ALEXANDRIA. VIRGINIA 22313

SIR:

Applicant(s) wish to disclose the following information.

REFERENCES

- The applicant(s) wish to make of record the references listed on the attached form PTO-1449. Copies of the listed references are attached, and copies were submitted in Application Serial No. 09/808,888 according to the attached copy of a Granted Petition. This application contains related subject matter.
- ☐ A check or credit card payment form is attached in the amount required under 37 CFR §1.17(p).

RELATED CASES

- Attached is a list of applicant's pending application(s), published application(s) or issued patent(s) which may be related to the present application. In accordance with the waiver of 37 CFR 1.98 dated September 21, 2004, copies of the cited pending applications are not provided. Cited published and/or issued patents, if any, are listed on the attached PTO form 1449.
- ☐ A check or credit card payment form is attached in the amount required under 37 CFR §1.17(p).

CERTIFICATION

- ☐ Each item of information contained in this information disclosure statement was first cited in any communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this statement.
- □ No item of information contained in this information disclosure statement was cited in a communication from a foreign patent office in a counterpart foreign application or, to the knowledge of the undersigned, having made reasonable inquiry, was known to any individual designated in 37 CFR §1.56(c) more than three months prior to the filing of this statement.

DEPOSIT ACCOUNT

Please charge any additional fees for the papers being filed herewith and for which no check or credit card payment is enclosed herewith, or credit any overpayment to deposit account number <u>15-0030</u>. A duplicate copy of this sheet is enclosed.

Respectfully submitted,

OBLON, SPIVAK, McCLELLAND,

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Form PTO 1449 U.S. DEPARTMENT OF COMMERCE (Modified) PATENT AND TRADEMARK OFFICE			ATTY DOCKET NO. 209284US99 0CT 1 8 200	4 8	SERIAL NO. 09/842,734			
					09/042,734	•		
LIST OF REFERENCES CITED BY APPLICANT Zhiyi YU, et al. FILING DATE GROUP								
				FILING DATE		GROUP		
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				U.S. PATENT DOCUMENTS		2011		
EXAMINER INITIAL		NUMBER	DATE	NAME	CLASS	CLASS IF APPROPRIATE		
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	ZW	6,232,806	05/15/01	WOESTE ET AL				
	ZX	5,430,397	07/04/95	ITOH ET AL				
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FOREIGN PATENT DOCUMENTS								
		DOCUMENT NUMBER	DATE	COUNTRY		TRANSLATION YES NO		
	ccs	WO 99/67882	12/29/99	WIPO				
	ССТ	WO 95/02904	01/26/95	WIPO		<u> </u>		
	CCU	WO 02/009150	01/31/02	WIPO				
	CCV	0 766 292	04/02/97	EUROPE				
	ccw	198 29 609	01/05/00	GERMANY				
	ссх	1 069 605	01/17/01	EUROPE				
	CCY	0 828 287	03/11/98	EUROPE		1		
	CCZ	1 176 230	01/30/02	EUROPE				
OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)								
* -	LLAP	YI W. et al; "Mechanism of cleaning Si (100) surface using Sr and SrO for the growth of crystalline SrTiO/sub 2/films" Journal of Vacuum Science & Technology, Vol. 20, No. 4, July 2002 (2002-07) pp. 1402-1405						
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	LLAR							
	LLAS			Additional References sheet(s) attached				
Examiner					Date Co	e Considered		
*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.								